

**Silicon PNP Power Transistors**

**2SA1185**

**DESCRIPTION**

- With TO-3PN package
- High current capability
- Low collector saturation voltage

**APPLICATIONS**

- High power amplifier applications

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

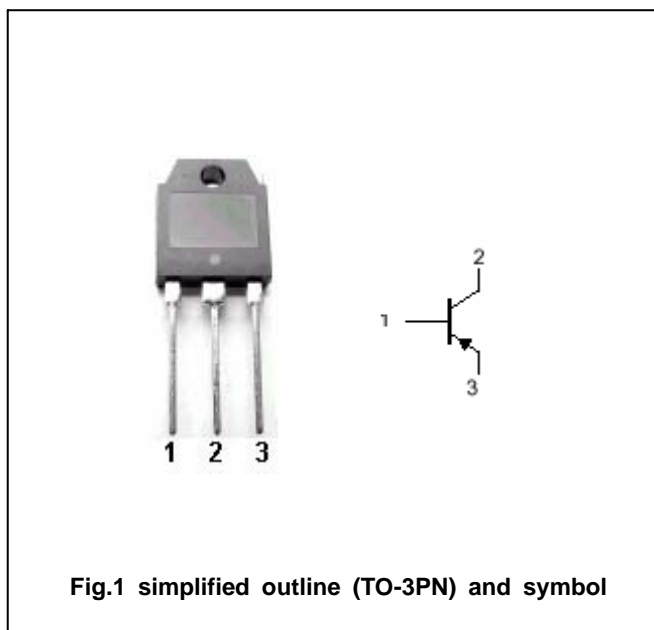


Fig.1 simplified outline (TO-3PN) and symbol

**Absolute maximum ratings(Ta= )**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-50	V
$V_{CEO}$	Collector-emitter voltage	Open base	-50	V
$V_{EBO}$	Emitter-base voltage	Open collector	-5	V
$I_C$	Collector current		-7	A
$I_{CM}$	Collector current-peak		-15	A
$I_{BM}$	Base current-peak		-5	A
$P_C$	Collector power dissipation	$T_C=25$	60	W
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-0.1A ; I <sub>B</sub> =0	-50			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-7A ; I <sub>B</sub> =-0.7A			-0.8	V
V <sub>BE</sub>	Base-emitter on voltage	I <sub>C</sub> =-7A ; V <sub>CE</sub> =-5V			-1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-50V ; I <sub>E</sub> =0			-1	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-5V ; I <sub>C</sub> =0			-2	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-5V	60		320	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =-7A ; V <sub>CE</sub> =-5V	20			
C <sub>ob</sub>	Output capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> =-10V ; f=1MHz		250		pF
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-0.5A ; V <sub>CE</sub> =-5V		100		MHz

◆ h<sub>FE-1</sub> Classifications

Q	P	O
60-120	100-200	160-320

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PACKAGE OUTLINE

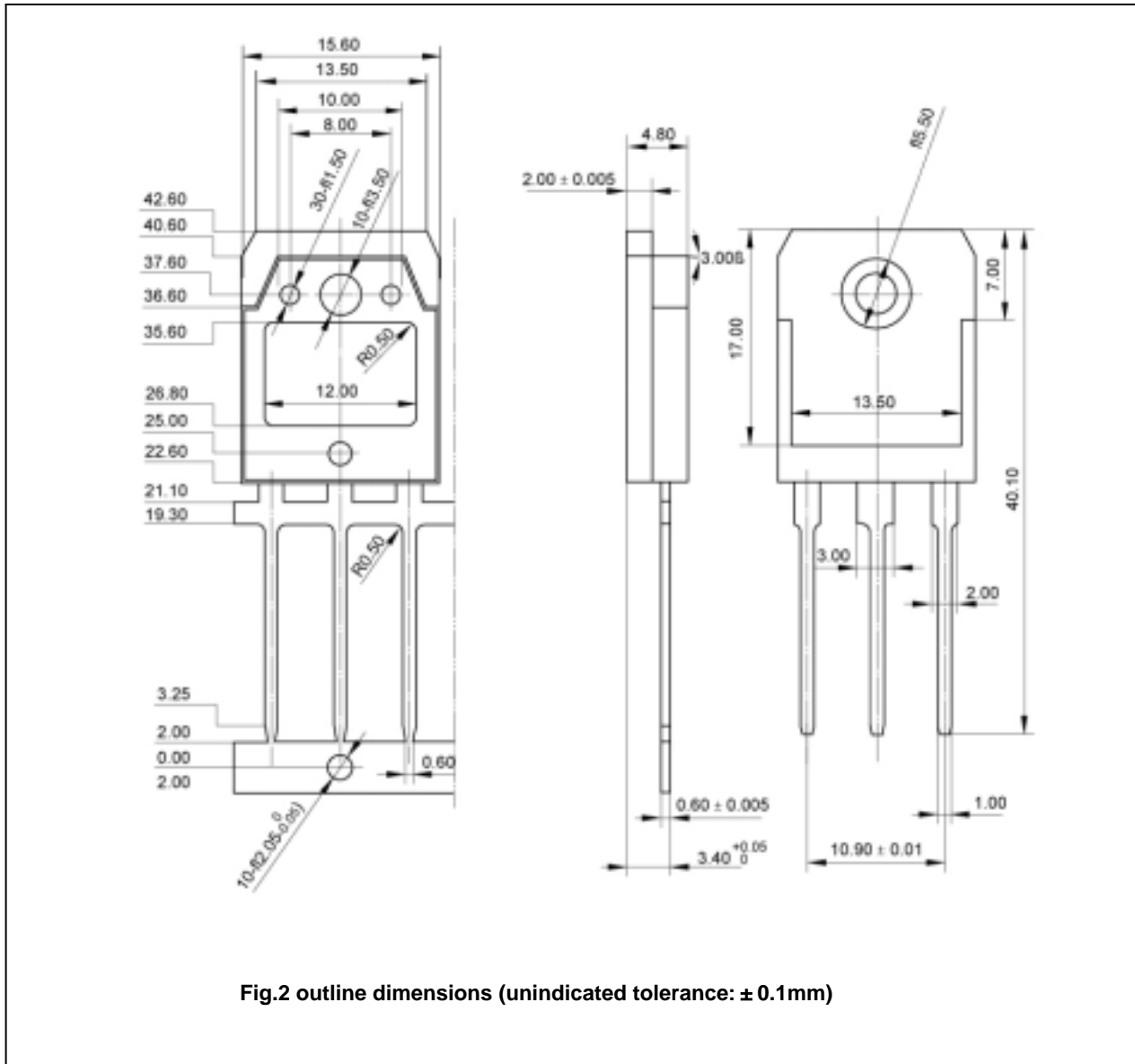


Fig.2 outline dimensions (unindicated tolerance: ± 0.1mm)